Activity description

Describe your work in a step by step list below, or submit a copy of your synthesis pathway. Please remove the examples before you hand in the form.

If you are doing characterization only, skip this section and fill out section Characterization only.

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1				
	Step		Risks involved Risk reducing measu	
	1	Wafer Clean (if necessary) Piranha solution (3xH ₂ SO ₄ +1x H ₂ O ₂)	Highly oxidising, reacts violently with organics, highly corrosive, exothermic, can reach 100°C	Fumehood; Wear apron, faceshield and acid gloves; no organics on surface, slowly mix peroxide into
		RCA Clean (if necessary) SC-1: 1xNH ₄ OH+1x H ₂ O ₂ +5x H ₂ O SC-2: 1x HCl +1x H ₂ O ₂ +5x H ₂ O	Corrosive, heated to 75°C	acid. Use heavy duty beakers and waste bottle with red cap.
		H ₂ O rinse and dry		PPE as for Piranha. Add acid/base to water, not other way round. Both require buddy
	2	Deposition of 1 st metal layer stack Sputter clean 20 nm Cr or Ti adhesion layer 200 nm Pt or Au electrode layer 20 nm Cr or Ti adhesion layer by sputter deposition or e-beam evaporation		
\bigcirc	3	Photolithography Dehydration bake Resist spin (S1823 or AZ9260), softbake at 115°C Exposure Development in MF319 or similar base Descum in O ₂ plasma	Solvent exposure	Do not inhale fumes
	4	1 st metal layer stack etching <u>Dry etch</u> : ICP-RIE using Cl ₂ & CF ₄ or sputter etching or	ICP-RIE: Need to consider platen temperature needs to be above 70°C at least to avoid redeposition of Pt, Au not currently possible – potential issues with resist at higher temperature, may need to use hardmask or sputter etch at lower temperatures instead, or consider wet etch (tried and tested)	Keep platen temperature below 70°C (?) if using resist in chamber. Do not exceed 500 V DC bias to avoid burning out Pt thermocouple in chamber, as advised by Oxford instruments

	Wet etch:		Apron, Faceshield, acid	
	Ti: 1xNH ₄ OH+2x H ₂ O ₂ (<100 ml)	Corrosive	gloves, extracted wet bench	
	Cr: CR14 (<100 ml) (22% ceric Corrosive		for al the metal wet etches.	
	ammonium nitrate, 9% glacial			
	acetic acid, 69% DI water, by			
	weight)			
	Au: 8g KI, 2g I ₂ , 80 ml DI water or			
	80 ml of transparent etch (20 g I2,			
	80 g NH₄l, 600 ml ethanol, 400 ml			
	dl H ₂ O)			
	Pt: pre-sputter in Ar plasma 2 min,	Highly Corrosive, reacts violently		
	then Aqua regia at 50°C (25 ml	with organics	In addition to above PPE,	
	HNO ₃ +50 ml HCl)		buddy is presumably	
	Photoresist strip in acetone		required for this, use small	
	10 min O ₂ plasma strip		amount only. No organics on	
-		surface		
5	O ₂ plasma clean PECVD deposition of insulator	Silane gas	Pump chamber/loadlock three times	
	PECVD deposition of insulator SiO ₂ , Si ₃ N ₄ or Al ₂ O ₃			
6	Photolithography (S1813)	As before	As before	
7	RIE etch of 1 st insulator	Click to write text	Click to write text	
	Using CHF ₃ , O ₂ , Ar			
	Photoresist strip in acetone			
	10 min O ₂ plasma strip			
8	Deposition of 2 nd metal layer	Click to write text	Click to write text	
	stack			
	Sputter clean			
	20 nm Cr or Ti adhesion layer			
	200 nm Pt or Au electrode layer			
	20 nm Cr or Ti adhesion layer			
	by sputter deposition or e-beam evaporation			
9	Photolithography (S1813)	As before	As before	
10	2 nd metal layer stack etching	As before	As before	
11	2 nd PECVD deposition of	As before	As before	
	insulator layer			
12	NIL	Need additional information on	Work in fume hood, wear	
	PDMS stamp preparation	this, I see one of the steps	suitable gloves and PPE	
	Amonil spin	requires an HF etch of the glass	-	
	SCIL nanoimprint on MA6 mask	carrier plate to remove micro-		
	aligner	cracks; is this really necessary?		
13	RIE etch of 2 nd insulator layer	As before	As before	
14	2 nd metal layer stack nanowell	As before	As before	
	etching			
	ICP-RIE using Cl ₂ & CF ₄			
15	RIE etch of 1 st insulator	As before	As before	
16	Photolithography	As before	As before	
17	Electroplating Ni/Au	Done externally	Done externally	
18	Photolithography	As before	As before	
19	Scribing/Dicing	Small particular matter	Wear gloves and safety	
			specs	

20	Flip Chip Mounting & Underfill Using solder beads <i>or</i> indium / gallium mix <i>or</i> wirebonder Underfill with UV curable epoxy or Masterbond EP30Med Acetone, IPA, H ₂ O clean	Gallium – suspected renal toxicity in large doses, potential for contact dermatitis Indium – considered non-toxic in pure form	Very small amounts used
21	O ₂ descum Silanisation	Silanes: Corrosive, harmful,	Safety Goggles, appropriate
	Vapour phase silanisation in dry N_2 or Ar atmosphere using max. 1-2 ml 3-APTES or 3-GEOPS. Bake at 120°C, wash in acetone, IPA, H ₂ O clean O ₂ descum	irritant; Harmful if swallowed. Causes burns.	gloves Use only in extracted wet bench.

What risks are involved in case power, process gases, N₂, water or pressurized air supply is cut?

Wet etching: Power supply loss would stop extraction of hazardous gases from fume hood. Loss of water supply would be hazardous in case of a spill

Equipment: valves actuated through pressurized air would stop to function, loss of water or liquid nitrogen would affect cooling on devices such as the PECVD/RIE and sputter coater.

Process gasses: Loss of nitrogen would prevent correct purge and pumpdown cycle to remove dangerous process gases from chamber and loadlock on PECVD/RIE

Comments to the steps above, if any

Characterization

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Instrument	Material to characterize	Comments
S(T)EM	Nanoholes through Au or Pt on	Sample size can be cut to fit
	Si3N4, SiO2, or Al2O3	instrument. Conducting and
		non-magnetic.
Dektak or other Profilometer	Photoresist and etched	
	metals/insulators on Si wafers	
Optical Microscope	Photoresist and etched	
	metals/insulators on Si wafers	
Interferometer	Photoresist and etched	
	metals/insulators on Si wafers	
AFM	200 nm or larger Nanoholes	
	through metal insulator	
	sandwich structure	

Information about all instruments listed can be found on ntnu.norfab.no

Comments to the information above, if any	

Chemicals

Only "Name of chemical" is needed if you do not know the other details. The chemical archive on <u>ecoonline.no</u> shows the chemicals that are provided by NanoLab, and if buddy/logging is needed. For guest log in: Code 1560, username and password "nano". Please remove the examples before you hand in the form.

If the chemicals will be heated, pressurized or mixed with other chemicals, a risk evaluation for this has to be submitted. NTNU's standard risk evaluation forms (found on LIMS, under Info) or any other format of your choice can be used.

NanoLab's licenses related to chemicals (chemical handling license + area courses) do not give any education in safe handling of chemicals. Supervision or previous experience is a prerequisite for chemical work in the cleanroom.

				Will be heated,
Name of chemical	Provided by	Buddy	Logging	pressurized or
Name of chemical	NanoLab	needed	needed	mixed with
				other chemicals
Ethanol (97%)	⊠Yes □No	🗌 Yes 🖾 No	□Yes ⊠No	🗌 Yes 🖾 No
Conc. Nitric acid	🖾 Yes 🗌 No	🖾 Yes 🗌 No	□Yes ⊠No	⊠Yes □No
Conc. Sulphuric acid	🖾 Yes 🗌 No	🖂 Yes 🗌 No	🗌 Yes 🖂 No	□Yes □No
Conc. Hydrochloric acid	🖾 Yes 🗌 No	⊠Yes □No	🗌 Yes 🖾 No	⊠Yes □No
Ammonium Hydroxide	🖾 Yes 🗌 No	⊠Yes □No	🗌 Yes 🖾 No	⊠Yes □No
Hydrogen peroxide 30%	🖾 Yes 🗌 No	🗌 Yes 🖾 No	□Yes ⊠No	⊠Yes □No
Tween-20	🗌 Yes 🖾 No	🗌 Yes 🖾 No	🗌 Yes 🖾 No	🗌 Yes 🖾 No
Biotin-PEG12-NHS Ester	□Yes ⊠No	□Yes ⊠No	□Yes ⊠No	🗌 Yes 🖾 No
Avidin	□Yes ⊠No	🗌 Yes 🖾 No	🗌 Yes 🖾 No	🗌 Yes 🖾 No
Streptavidin	🗌 Yes 🖾 No	🗌 Yes 🖾 No	□Yes ⊠No	🗌 Yes 🖾 No
Guanidine hydrochloride	□Yes ⊠No	🗌 Yes 🖂 No	🗌 Yes 🖾 No	□ Yes ⊠No
Ethylenediaminetetraacetic acid	□Yes ⊠No	🗌 Yes 🖾 No	□Yes ⊠No	🗌 Yes 🖾 No
(EDTA)				
Acetone	🖾 Yes 🗌 No	🗌 Yes 🖾 No	🗌 Yes 🖾 No	🗌 Yes 🖾 No
IPA	🖾 Yes 🗌 No	🗌 Yes 🖂 No	□Yes ⊠No	🗌 Yes 🖾 No
3-aminopropyltriethoxysilane	🗌 Yes 🖾 No	🗌 Yes 🗌 No	🗌 Yes 🗌 No	🛛 Yes 🗌 No
(3-Glycidyloxy-	🗌 Yes 🖾 No	🗌 Yes 🗌 No	🗌 Yes 🗌 No	🖾 Yes 🗌 No
propyl)trimethoxysilane				
S1813	🖾 Yes 🗌 No	🗌 Yes 🖾 No	🗌 Yes 🖾 No	🗌 Yes 🖾 No
S1805	🗌 Yes 🖾 No	🗌 Yes 🖾 No	🗌 Yes 🖾 No	□ Yes ⊠No
S1823	🗌 Yes 🖾 No	🗌 Yes 🗌 No	□Yes □No	□ Yes ⊠No
AZ9260	🗌 Yes 🖂 No	🗌 Yes 🖾 No	□ Yes ⊠No	□ Yes ⊠No

Comments to the information above, if any

Silanes will be used in PDMS area

AZ 9260 is introduced in activity NL0132